CLAIMS

1. A process for the production of a semiconductor substrate comprising an epitaxially deposited layer, successively comprising the following stages:

- etching a susceptor of an epitaxy reactor;
- coating the susceptor;
- installation of a semiconductor substrate on the susceptor;
- deposition of an epitaxial layer on the semiconductor substrate;

and additionally, after the coating and before the deposition, the exposure of the susceptor to an oxygen-containing gas mixture, said exposure resulting in an oxidation of the susceptor which will form an oxide layer at the surface of the susceptor, said oxide layer being found, during the deposition of the epitaxial layer on a front face of the semiconductor substrate, inserted between the susceptor and a rear face of the semiconductor substrate;
and additionally, after the installation and before the deposition, a baking of the semiconductor substrate which removes said oxide layer except on the underside of the semiconductor substrate.

2. The process as claimed in claim 1, in which the oxygen-comprising gas mixture is a mixture of hydrogen and of argon comprising between 0.1% and 10% of $O_2$.

3. The process as claimed in claim 2, in which $O_2$ is introduced into the epitaxy reactor at a flow rate of between 0.1 and 10 slm.

4. The process as claimed in one of claims 1 to 3, in which the oxide layer formed by the exposure of the susceptor to the oxygen-containing gas mixture exhibits a thickness of less than 10 Å.

5. The process as claimed in one of claims 1 to 4, in which said exposure is carried out after the coating and before said installation.

6. The process as claimed in claim 5, in which the stages of installation of a semiconductor substrate on the susceptor and of deposition of an epitaxial layer on the semiconductor substrate are repeated for at least one other semiconductor substrate without in the meantime etching, coating and exposing the susceptor to an oxygen-containing gas mixture.

7. The process as claimed in any one of claims 1 to 4, in which said exposure is carried out after said installation and before said deposition.

8. The process as claimed in claim 7, in which said exposure is carried out while increasing the temperature of the epitaxy reactor to an epitaxial deposition temperature.

9. The process as claimed in either of claims 7 and 8, in which the stages of installation of a semiconductor substrate on the susceptor, of exposure of the susceptor and of deposition of an epitaxial layer on the semiconductor substrate are repeated for at least one other semiconductor substrate without in the meantime etching and coating the susceptor.